ID(A)

6

5

Dual N-Channel 20-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

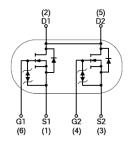
- Battery Powered Instruments
- Portable Computing
- Mobile Phones
- GPS Units and Media Players



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VDS (V)

20



PRODUCT SUMMARY

 $r_{DS(on)}(\overline{m\Omega})$

20 @ V_{GS} = 4.5V

28 @ V_{GS} = 2.5V

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V_{GS}	±8	v	
Continuous Drain Current ^a	T _A =25°C		6		
	T _A =100°C	I _D	3.6	А	
Pulsed Drain Current ^b		I _{DM}	22		
Continuous Source Current (Diode Conduction) ^a		ا _s	1	А	
Power Dissipation ^a	T _A =25°C	P _D	0.83	W	
	T _A =100°C	١D	0.3	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	С°	

FREE

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Maximum Junction-to-Ambient ^a	t <= 10 sec	R _{eja}	110	°C/W	
	Steady State	ιν _θ ja	150	C/VV	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, ID = 250 uA	20			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±10	uA	
Zero Gate Voltage Drain Current		$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 85^{\circ}\text{C}$			30		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			A	
Drain-Source On-Resistance	r	$V_{GS} = 4.5 \text{ V}, I_{D} = 6 \text{ A}$			20	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_{D} = 5 \text{ A}$			28		
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 6 \text{ A}$		10		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 1.0 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
		Dynamic					
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6 \text{ A}$		13.5			
Gate-Source Charge	Q _{gs}			0.9		nC	
Gate-Drain Charge	Q_gd			5.4			
Turn-On Delay Time	t _{d(on)}			6			
Rise Time	t _r	$\begin{split} V_{\text{DD}} &= 10 \text{ V}, \text{R}_{\text{L}} = 10 \Omega \text{ , } \text{I}_{\text{D}} = 1 \text{A}, \\ V_{\text{GEN}} &= 4.5 \text{ V}, \text{R}_{\text{GEN}} = 6 \Omega \end{split}$		12		DC	
Turn-Off Delay Time	t _{d(off)}			65		ns	
Fall Time	t _f			35			
Input Capacitance	C _{iss}			680			
Output Capacitance	C _{oss}	V_{DS} = 10 V, V_{GS} = 0 V, f =1 MHz		144		рF	
Reverse Transfer Capacitance	C _{rss}			137			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

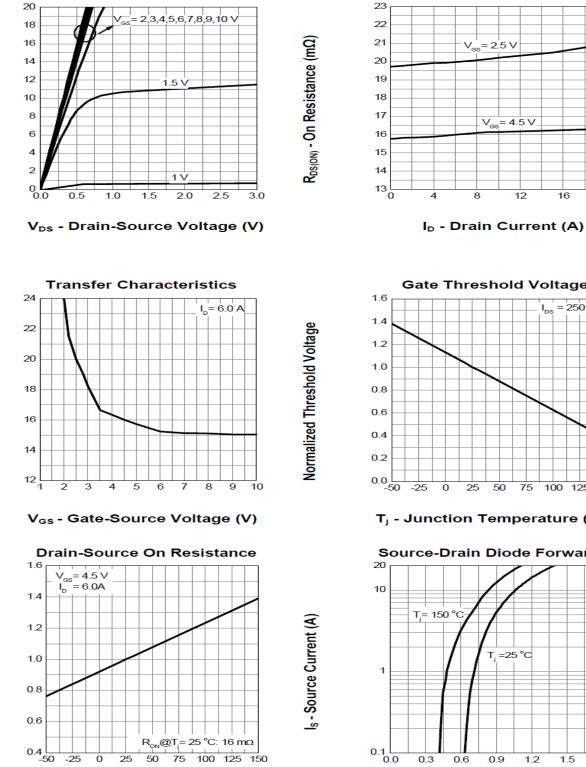
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Typical Electrical Characteristics

Output Characteristics





T_j - Junction Temperature (°C)

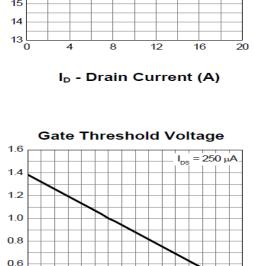
75

100 125 150

25 50

-25 0

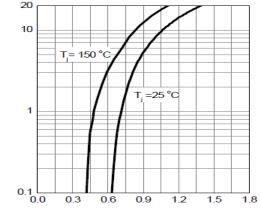
Drain-Source On Resistance



75 100 125 150

T_j - Junction Temperature (°C)

Source-Drain Diode Forward

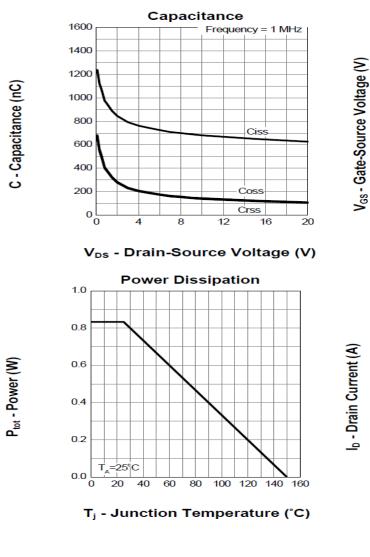


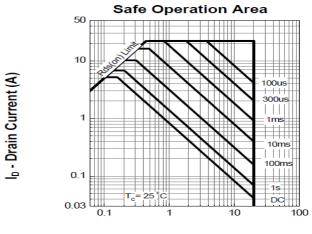
V_{sD} - Source-Drain Voltage (V)

R_{Ds(ON)} - On Resistance (mΩ)

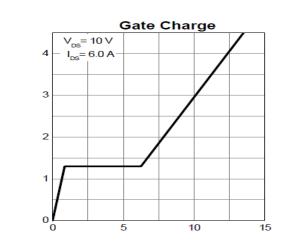
Normalized On Resistance

Typical Electrical Characteristics

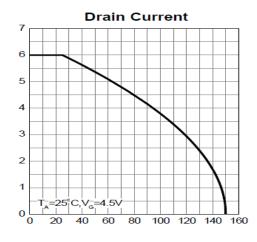




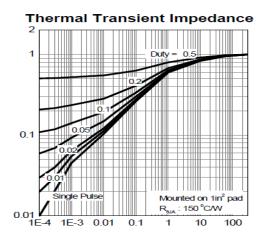
V_{DS} - Drain-Source Voltage (V)



Q_G - Gate Charge (nC)



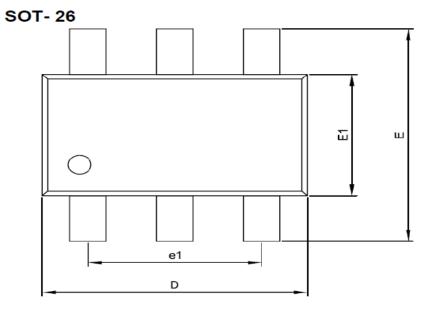
T_j - Junction Temperature (°C)

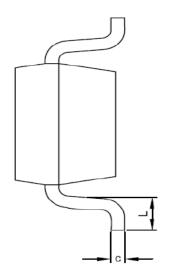


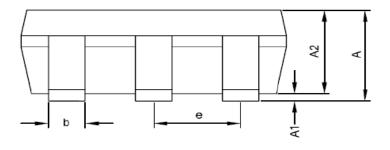
Square Wave Pulse Duration (sec)

Normalized Effective Transient

Package Information







Symbol	Dimensions In Millimeters		
Symbol MIN.		MAX.	
А		1.45	
A1		0.15	
A2	0.9	1.3	
D	2.90 BSC		
E	2.890 BSC		
E1	1.5	1.7	
С	0.08	0.25	
b	0.3	0.5	
е	0.95BSC		
e1	1.90BSC		
L	0.3	0.6	